

BCW32**NPN EPITAXIAL SILICON TRANSISTOR**

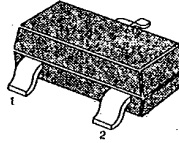
T-29-19

GENERAL PURPOSE TRANSISTOR**ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CE0}	20	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBT5088 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=10\mu\text{A}, I_E=0$	30		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=2\text{mA}, I_B=0$	20		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=10\mu\text{A}, I_C=0$	5		V
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}, I_C=2.0\text{mA}$	200	450	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		0.25	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=2\text{mA}, V_{CE}=5\text{V}$	0.55	0.7	V
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0$ $f=1.0\text{MHz}$		4	pF
Noise Figure	NF	$I_C=0.2\text{mA}, V_{CE}=5\text{V}$ $R_S=2\text{K}\Omega, f=1\text{KHz}$		10	dB

Marking

